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(71) Applicant: MICRON TECHNOLOGY, INC. [US/US]; 8000 South Federal Way, Boise, ID 83716 (US).

(72) Inventors: CAMPBELL, Kristy, A.; 9845 West Mossy Cup Street, Boise, ID 83709 (US). MOORE, John, T.; 12530 West Lexus Court, Boise, ID 83713 (US).

(74) Agents: MATKIN, Mark, S. et al.; Micron Technology, Inc., 8000 South Federal Way, Boise, ID 83716 (US).

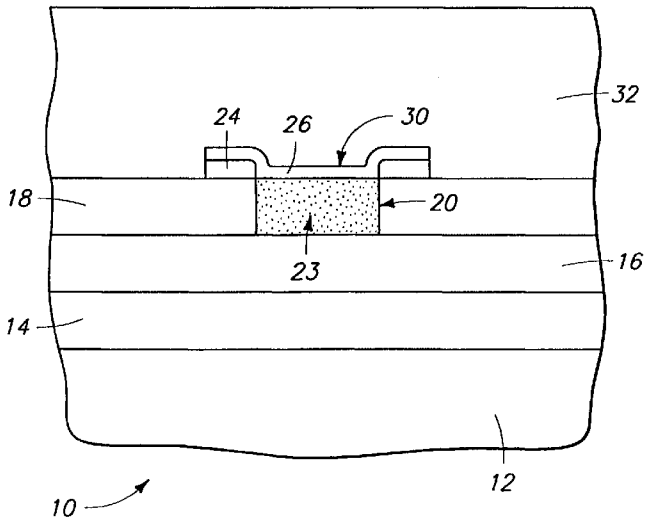
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(54) Title: METHOD OF FORMING NON-VOLATILE RESISTANCE VARIABLE DEVICES AND METHOD OF FORMING A PROGRAMMABLE MEMORY CELL OF MEMORY CIRCUITRY



(57) Abstract: A first conductive electrode material is formed on a substrate. Chalcogenide comprising material is formed thereover. The chalcogenide material comprises A_xSe_y. A silver comprising layer is formed over the chalcogenide material. The silver is irradiated effective to break a chalcogenide bond of the chalcogenide material at an interface of the silver comprising layer and chalcogenide material and diffuse at least some of the silver into the chalcogenide material. After the irradiating, the chalcogenide material outer surface is exposed to an iodine comprising fluid effective to reduce roughness of the chalcogenide material outer surface from what it was prior to the exposing. After the exposing, a second conductive electrode material is deposited over the chalcogenide material, and which is continuous and completely covering at least over the chalcogenide material, and the second conductive electrode material is formed into an electrode of the device.

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